

ABSTRACT

The present invention relates to a semiconductor manufacturing component for manufacturing a semiconductor device by using a substrate such as a wafer in a dry etching process, and a manufacturing method thereof. The semiconductor manufacturing component comprising a deposition layer covering an interlayer boundary according to the present invention comprises: a base material containing carbon; a first deposition layer formed on the base material; a second deposition layer formed on the first deposition layer; and a third deposition layer formed on the first deposition layer and the second deposition layer, and formed to cover at least one portion of a boundary line between the first deposition layer and the second deposition layer.